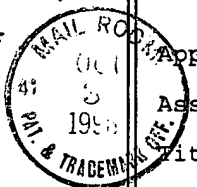


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicants: Constantin Bulucea and Rebecca Rossen
 Assignee: Siliconix incorporated
 Title: TRENCH DMOS POWER TRANSISTOR WITH FIELD-SHAPING
 BODY PROFILE AND THREE-DIMENSIONAL GEOMETRY
 Serial No.: 08/453,285 Filed: 5/30/95
 Examiner: J. Carroll Group Art Unit: 2508
 Attorney Docket No.: M-799-3C US

San Jose, California
 September 30, 1996

COMMISSIONER OF PATENTS AND TRADEMARKS
 Washington, D. C. 20231

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AMENDMENT

GROUP 2500

Sir:

In response to the Office Action of April 4, 1996, please
 amend the above-referenced patent application as follows:

IN THE CLAIMS

Please cancel Claims 45 and 66.

In Claim 42, at line 9, please delete "second" and
 substitute --first--.

In Claim 63, at line 9, please delete "second" and
 substitute --first--.

In Claim 64, at line 1, please delete "32" and substitute
 --54--.

Please amend Claims 30, 54, 56 and 58 as follows:

30. (Twice amended) A trench DMOS transistor cell,
 comprising:

a substrate of semiconductor material of a first
 electrical conductivity type having a top surface;

a first covering layer of semiconductor material of
 said first electrical conductivity type, said first
 covering layer (i) having a dopant concentration less than
 that of said substrate, (ii) having a top surface and
 (iii) being contiguous to and overlying the substrate top
 surface;

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